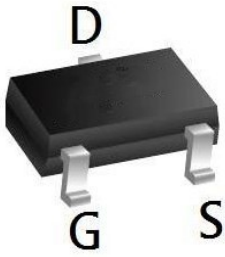
P-Ch 20V Fast Switching MOSFETs

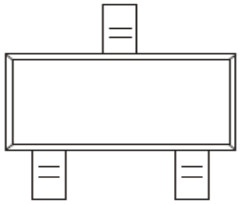
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	RDSON	ID
-20V	500mΩ	-0.66A

SOT523 Pin Configuration



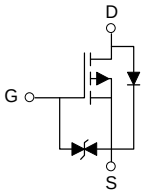


Description

The XXW3139 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The XXW3139 meet the RoHS and Green Product requirement with full function reliability approved.

ESD Rating: 2000V HBM



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I_D	-0.66	A
Pulsed Drain Current (t_p=10μs)	I_{DM}	-1.2	A
Power Dissipation (note 1)	P_D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃
Lead Temperature for Soldering Purposes(1/8” from case for 10 s)	T_L	260	℃

T_a=25℃ unless otherwise specified

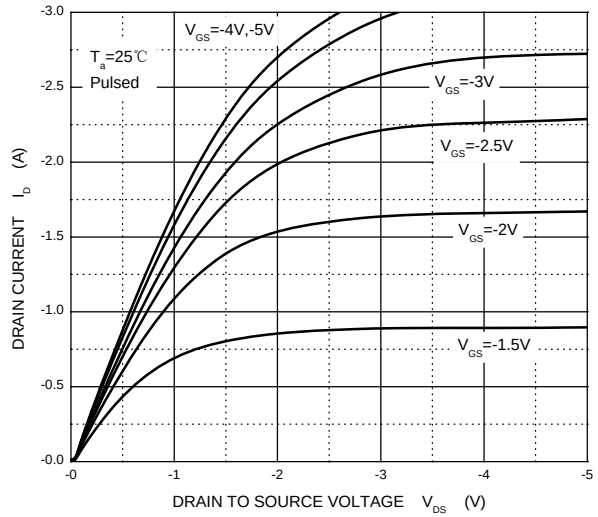
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V,V_{GS} = 0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±10V, V_{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.35		-1.1	V
Drain-source on-resistance (note 2)	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-1A			520	mΩ
		V_{GS} =-2.5V, I_D =-0.8A			700	mΩ
		V_{GS} =-1.8V, I_D =-0.5A		950		mΩ
Forward transconductance (note 2)	g_{FS}	V_{DS} =-10V, I_D =-0.54A		1.2		S
Diode forward voltage	V_{SD}	I_S=-0.5A, V_{GS} = 0V			-1.2	V
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	V_{DS} =-16V,V_{GS} =0V,f =1MHz		113	170	pF
Output capacitance	C_{oss}			15	25	pF
Reverse transfer capacitance	C_{rss}			9	15	pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time (note 3)	$t_{d(on)}$	V_{GS}=-4.5V,V_{DS}=-10V, I_D =-200mA,R_{GEN}=10Ω		9		ns
Turn-on rise time (note 3)	t_r			5.8		ns
Turn-off delay time (note3)	$t_{d(off)}$			32.7		ns
Turn-off fall time (note 3)	t_f			20.3		ns

Notes :

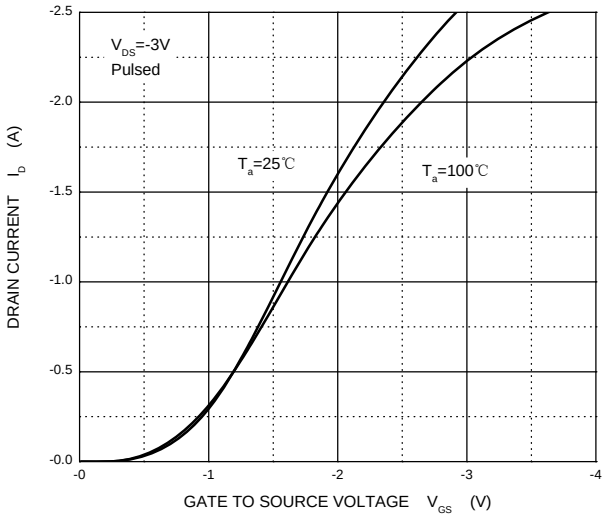
1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300μs, Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

Typical Characteristics

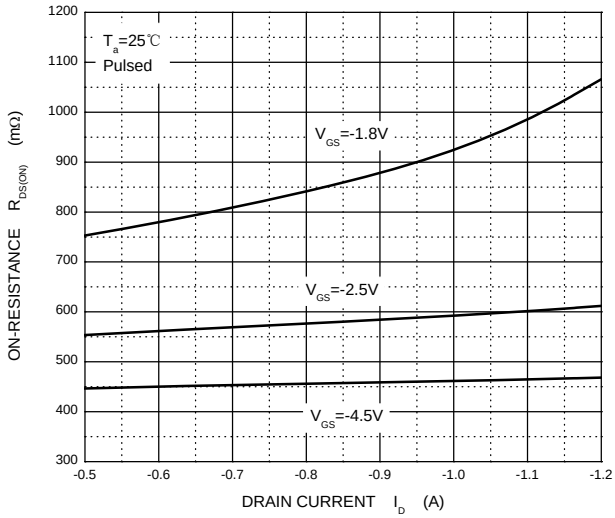
Output Characteristics



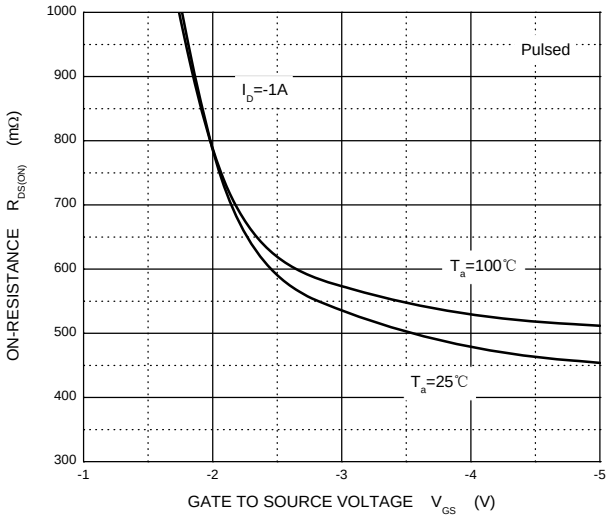
Transfer Characteristics



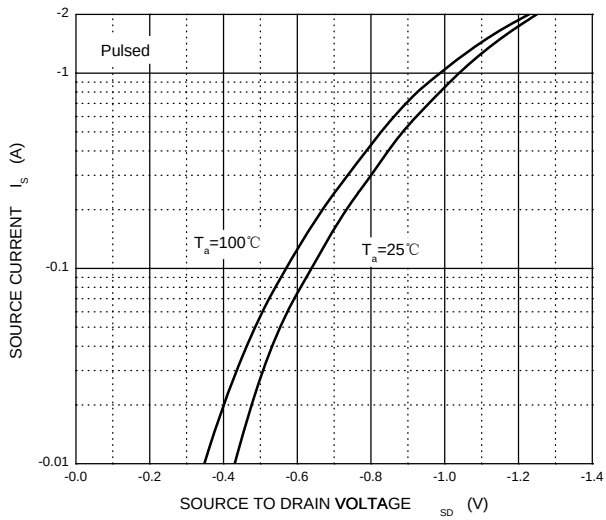
$R_{DS(ON)}$ —— I_D



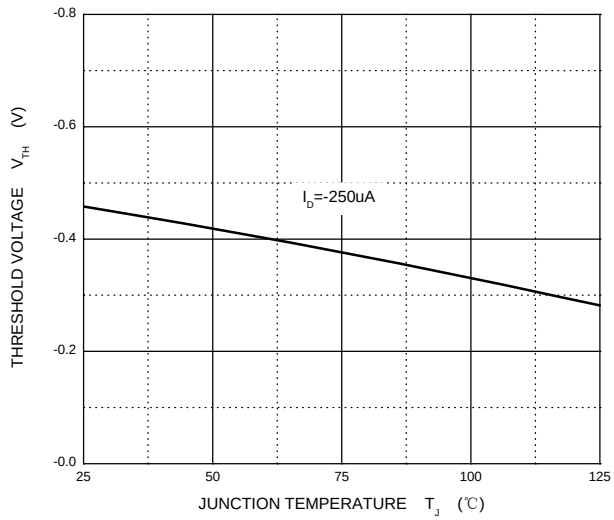
$R_{DS(ON)}$ —— V_{GS}



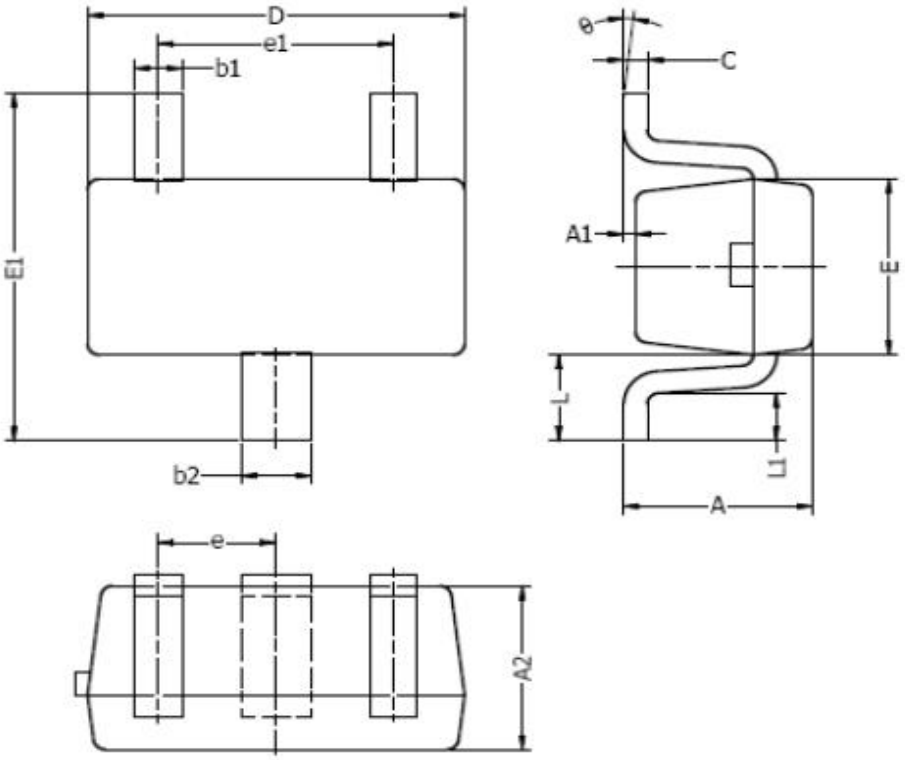
I_S —— V_{SD}



Threshold Voltage



Package Mechanical Data-SOT-523



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:
1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.